



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jonathan J. Wierer, Jr., Michael R. Krames, John E. Epler
Assignee: Lumileds Lighting U.S., LLC
Title: Photonic Crystal Light Emitting Device
Serial No.: 10/804,810 Filing Date: March 19, 2004
Examiner: Ho, Tu Tu V Group Art Unit: 2818
Docket No.: LUM-03-05-01

San Jose, California
July 27, 2005

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

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UNDER 37 CFR § 1.97(b)

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Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying forms PTO/SB/08A and PTO/SB/08B are called to the attention of the Examiner for the above patent application. Copies of the cited foreign patent documents and articles are enclosed. Copies of the cited US Patent documents are not enclosed as the requirement under 37 CFR 1.98 (a)(2)(i) is waived.

Citation of these documents shall not be construed as:

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2. a representation that a search has been made; or
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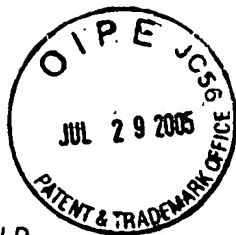
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Respectfully submitted,

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Group Art Unit: 2818

Dear Sir:

Transmitted herewith are the following documents in the above-identified application:

- (1) Return Receipt Postcard;
- (2) This Transmittal Letter;
- (3) Information Disclosure Statement (1 page);
- (4) Forms PTO/SB/08A and PTO/SB/08B citing 46 references (4 pages);
- (5) Twenty seven (27) cited references;
- (6) Copies of the cited US Patent documents are not enclosed as the requirement under 37 CFR 1.98 (a)(2)(i) is waived.

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Rachel V. Leiterman
Attorney for Applicant(s)
Reg. No. 46,868



PTO/SB/08A (08-03)

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STATEMENT BY APPLICANT**

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Sheet 1

of 4

Complete if Known

Application Number	10/804,810
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First Named Inventor	Jonathan J. Wierer Jr.
Art Unit	2818
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Attorney Docket Number	LUM-03-05-01

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US- 2002/0130311 A1	9-19-2002	Lieber et al.	
		US- 2003/0089899 A1	5-15-2003	Lieber et al.	
		US- 2004/0213307 A1	10-28-2004	Lieber et al.	
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		US- 5,371,025	12-6-1994	Sung	
		US- 6,831,302 B2	12-14-2004	Erchak et al.	
		US- 2005/0145877 A1	7-7-2005	Erchak	
		US- 2005/0127375 A1	6-16-2005	Erchak et al.	
		US- 2005/0087757 A1	4-28-2005	Erchak et al.	
		US- 2005/0087754 A1	4-28-2005	Erchak	
		US- 2005/0051787 A1	3-10-2005	Erchak et al.	
		US- 2005/0051785 A1	3-10-2005	Erchak et al.	
		US- 2005/0040424 A1	2-24-2005	Erchak et al.	
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		US- 2004/0207320 A1	10-21-2004	Erchak	
		US- 2004/0109644 A1	6-10-2004	Assefa et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
		WO 2004/004927 A2	1-15-2004	BTG International		
		WO 2004/032193 A2	4-15-2004	Nanosys, Inc.		
		WO 2004/034025 A2	4-22-2004	Nanosys, Inc.		
		WO 2004/038767 A2	5-6-2004	President and Fellows		
		EP 0 874 405 A2	10-28-1998	Mitsubishi Cable Ind.		
		WO 03/023857 A2	3-20-2003	Lucea Ag		

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Sheet	2	of	4
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U. S. PATENT DOCUMENTS

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		Country Code ³ *Number ⁴ *Kind Code ⁵ <i>(if known)</i>				
		EP 1 071 143 A1	1-24-2001	Mitsubishi Cable Ind.		

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		First Named Inventor	Jonathan J. Wierer,		
		Art Unit	Not yet assigned		
		Examiner Name	Not yet assigned		
Sheet	3	of	4	Attorney Docket Number	LUM-03-05-01

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		M. FUJITA et al., "Organic light-emitting diode with ITO/organic photonic crystal," Electronics Letters, 27th November 2003, Vol. 39, No. 24, 2 pages.	
		T.N. ODER et al., "III-nitride blue and ultraviolet photonic crystal light emitting diodes," Applied Physics Letter, Vol. 84, No. 4, 26 January 2004, pp. 466-468.	
		HIROYUKI ICHIKAWA et al., "Efficiency enhancement in a light-emitting diode with a two-dimensional surface grating photonic crystal," Applied Physics Letters, Vol. 84, No. 4, 26 January 2004, pp. 457-459.	
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		T. HAMANO et al. "New Technique for Fabrication of Two-Dimensional Photonic Bandgap Crystals by Selective Epitaxy," Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L286 to L288.	
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		G. KIPSHIDZE et al., "Controlled growth of GaN nanowires by pulsed metalorganic chemical vapor deposition," Applied Physics Letters 86, (2005) American Institute of Physics, pp. 033104-1 to 033104-3.	
		KWA-MOK KIM et al., "Growth and characterization of single-crystal GaN nanorods by hydride vapor phase epitaxy," Applied Physics Letters, Vol. 81, No. 12, 16 September 2002, pp. 2193 to 2195.	
		S. HAN et al, "Controlled growth of gallium nitride single-crystal nanowires using a chemical vapor deposition method," J. Mater. Res., Vol. 18, No. 2, Feb. 2003, Materials Research Society, pp. 245 to 249.	

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		HWA-MOK KIM, et al., "Nanoscale Ultraviolet-Light-Emitting Diodes Using Wide-Bandgap Gallium Nitride Nanorods," Adv. Mater.2003, 15, No. 7-8, April 17, WILEY-VCH Verlag GmbH & Co. KGaA, Weinheim, pp. 567 to 569.	
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		V.V. MAMUTIN, et al., "Growth of Self-Organized GaN Nanostructures on Al ₂ O ₃ (0001) by RF MBE., Proc. Int. Workshop on Nitride Semiconductors, IPAP Conf. Series 1, pp. 413 to 416.	
		J. SU et al., "Catalytic growth of group III-nitride nanowires and nanostructures by metalorganic chemical vapor deposition," Applied Physics Letters 86, (2005), American Institute of Physics, pp. 013105-1 to 013105-3.	
		W. D. ZHOU et al, "Electrically injected single-defect photonic bandgap surface-emitting laser at room temperature," Electronic Letters, 31st August 2000, Vol. 36, No. 18, pp. 1541 to 1542.	
		P. BHATTACHARYA et al., "Electrically Injected Photonic Bandgap Microcavity Light Sources," LEOS 2001 14th. Annual Meeting of the IEEE Lasers & Electro-Optics Society, San Diego, Ca, Nov. 11-15, Vol 1 of 2, pp. 76 to 77.	
		S. KITAMURA et al, "Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates via Selective Metalorganic Vapor Phase Epitaxy, Jpn. J. Appl. Phys., Vol. 34 (1995), Part 2, No. 9B, 15 September 1995, pp. L1184 to L1186.	
		M. NAGAHARA et al., "Selective Growth of Cubic GaN in Small Areas on Patterned GaAs (100) Substrates by Metalorganic Vapor Phase Epitaxy," Jpn. J. Appl. Phys., Vol. 33 (1994), Part 1, No. 1B, January 1994, pp. 694 to 697.	
		A. KIKUCHI et al., "Self-Organized InGaN/GaN Multiple Quantum Well Nanocolumn Light Emitting Diodes Grown On (111) Si Substrate," Department of Electrical and Electronics Engineering, Sophia University, 1 page.	

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